

ABSTRACT OF THE DISCLOSURE

To provide a semiconductor nonvolatile storage device capable of applying distributed voltage efficiently to a ferroelectric capacitor in a semiconductor nonvolatile storage device having an MFMIS structure without enlarging a memory cell area and a method of fabricating the same, a ferroelectric nonvolatile storage element is constructed by a structure successively laminated with a first insulator layer (3), a first conductor layer (4), a ferroelectric layer (5) and a second conductor layer (6) on a channel region and is constructed by a structure having a third conductor (9) and a fourth conductor (10) respectively laminated on a source region and a drain region, in which the third conductor (9) and the fourth conductor (10) are opposed to each other via the first conductor layer (4) and a second insulator thin film (11).